TECHNICAL DATA DATA SHEET 4157, REV. -

HERMETIC POWER SCHOTTKY RECTIFIER Very Low Forward Voltage

Applications:

· Switching Power Supply · Converters · Free-Wheeling Diodes · Polarity Protection Diode

Features:

- Soft Reverse Recovery at Low and High Temperature
- Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics

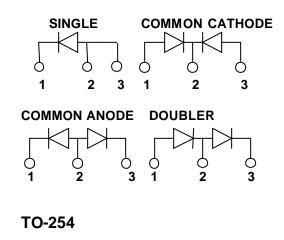
Maximum Ratings:

Characteristics	Symbol	Condition Max.		Units
Peak Inverse Voltage	V_{RWM}	-	45	V
Max. Average Forward	I _{F(AV)}	50% duty cycle, rectangular	15	Α
Current	, ,	wave form (Single/Doubler)		
Max. Average Forward	I _{F(AV)}	50% duty cycle, rectangular	30	Α
Current		wave form (Common		
		Cathode/Common Anode)		
Max. Peak One Cycle Non-	I _{FSM}	8.3 ms, half Sine wave	200	Α
Repetitive Surge Current		(per leg)		
Max. Thermal Resistance	$R_{\theta JC}$	(Single)	1.45	°C/W
Max. Thermal Resistance	$R_{\theta JC}$	(Common Cathode/Common	0.72	°C/W
		Anode/Doubler) (per leg)		
Max. Junction Temperature	T _J	-	-65 to +150	°C
Max. Storage Temperature	T _{stg}	-	-65 to +150	°C

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V_{F1}	@ 15A, Pulse, T _J = 25 °C	0.65	V
		(per leg)		
	V_{F2}	@ 15A, Pulse, T _J = 125 °C	0.60	V
		(per leg)		
Max. Reverse Current	I_{R1}	@V _R = 45V, Pulse,	1.5	μΑ
		$T_J = 25$ °C (per leg)		
	I _{R2}	@V _R = 45V, Pulse,	70	mA
		T _J = 125 °C (per leg)		
Max. Junction Capacitance	C _T	$@V_R = 5V, T_C = 25 ^{\circ}C$	800	pF
		$f_{SIG} = 1MHz,$		
		$V_{SIG} = 50 \text{mV (p-p) (per leg)}$		

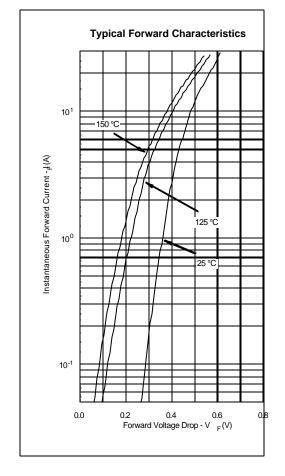
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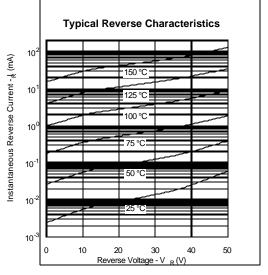


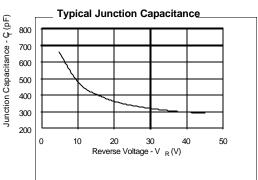
PINOUT TABLE

TYPE	PIN 1	PIN 2	PIN 3
SINGLE RECTIFIER	CATHODE	ANODE	ANODE
DUAL RECTIFIER, COMMON CATHODE (P)	ANODE 1	COMMON CATHODE	ANODE 2
DUAL RECTIFIER, COMMON ANODE (N)	CATHODE 1	COMMON ANODE	CATHODE 2
DUAL RECTIFIER, DOUBLER (D)	ANODE	CATHODE/ANODE	CATHODE

Note: The V_f curves shown are for the SD125SA45 un-packaged die only.









TECHNICAL DATA

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